

ABSTRACT OF THE DISCLOSURE

An apparatus and a method of fabricating a semiconductor device including the steps of forming a gate dielectric layer on a semiconductor substrate; forming a gate electrode over the gate dielectric layer wherein the gate electrode defines a channel interposed between source/drain regions formed within an active region of the semiconductor substrate; and forming contact etch resistant spacers on sidewalls of the gate electrode and sidewalls of the gate dielectric layer, the contact etch resistant spacers are of a non-silicon oxide and a non-nitride material.

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